


## SOT-227 Power Module Single Switch - Power MOSFET, 400 A



SOT-227

**FEATURES**

- $I_D = 400\text{ A}$ ,  $T_C = 25\text{ °C}$
- ThunderFET Power MOSFET
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Reduced switching and conduction losses
- Ultra low gate charge ( $Q_g$ )
- Maximum 175 °C junction temperature
- UL approved file E78996 
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS  
COMPLIANT**
**PRIMARY CHARACTERISTICS**

$V_{DSS}$	150 V
$R_{DS(on)}$ at 200 A	1.93 m $\Omega$
$I_D$	300 A at 90 °C
Type	Modules - MOSFET
Package	SOT-227

**APPLICATIONS**

- DC/DC conversions
- Motor drives
- DC/AC inverter
- Power supplies
- Uninterruptible power supplies
- AC/DC switch-mode power supplies

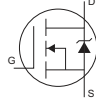
**ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
<b>MOSFET</b>				
Drain to source voltage	$V_{DSS}$		150	V
Continuous drain current, $V_{GS}$ at 10 V	$I_D$	$T_C = 25\text{ °C}$	400	A
		$T_C = 90\text{ °C}$	300	
Pulsed drain current	$I_{DM}^{(1)}$		860	
Power dissipation	$P_D$	$T_C = 25\text{ °C}$	909	W
Gate to source voltage	$V_{GS}$		$\pm 20$	V
Single pulse avalanche current	$E_{AS}$		720	J
Avalanche current	$I_{AS}$	$T_C = 25\text{ °C}$ , $L = 10\text{ mH}$ , $V_{GS} = 10\text{ V}$	120	A
<b>MODULE</b>				
Operating junction temperature range	$T_J$		-55 to +175	°C
Operating storage temperature range	$T_{Stg}$		-40 to +150	
Insulation voltage (RMS)	$V_{ISOL}$	any terminal to case, $t = 1\text{ min}$	2500	V

**Note**
<sup>(1)</sup> Limited at max. junction temperature

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Operating junction temperature range	$T_J$		-55	-	175	°C
Operating storage temperature range	$T_{Stg}$		-40	-	150	
Junction to case	MOSFET $R_{thJC}$		-	-	0.165	°C/W
Case to heatsink	Module $R_{thCS}$	Flat, greased surface	-	0.1	-	
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf. in)
		Torque to heatsink	-	-	1.3 (11.5)	Nm (lbf. in)
Case style			SOT-227			

ELECTRICAL CHARACTERISTICS ( $T_J = 25\text{ °C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain to source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = 500\text{ }\mu\text{A}$	150	-	-	V
Breakdown voltage temperature coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	Reference to $25\text{ °C}$ , $I_D = 1.0\text{ mA}$	-	9.0	-	mV/°C
Static drain to source on-resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 200\text{ A}$	-	1.93	2.75	mΩ
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 1.0\text{ mA}$	1.80	3.46	5.4	V
Temperature coefficient of threshold voltage	$\Delta V_{GE(th)}/\Delta T_J$	$V_{DS} = V_{GS}$ , $I_D = 1.0\text{ mA}$ ( $25\text{ °C}$ to $125\text{ °C}$ )	-	9.6	-	mV/°C
Forward transconductance	$g_{fs}$	$V_{DS} = 15\text{ V}$ , $I_D = 100\text{ A}$ , $V_{GS} = 10\text{ V}$	-	200	-	S
Drain to source leakage current	$I_{DSS}$	$V_{DS} = 150\text{ V}$ , $V_{GS} = 0\text{ V}$	-	0.5	10.0	μA
		$V_{DS} = 150\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 150\text{ °C}$	-	19	-	
Gate to source leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$	-	-	± 200	nA
Total gate charge	$Q_g$	$I_D = 250\text{ A}$ $V_{DS} = 75\text{ V}$ $V_{GS} = 10\text{ V}$	-	250	-	nC
Gate to source charge	$Q_{gs}$		-	79	-	
Gate to drain ("Miller") charge	$Q_{gd}$		-	82	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 75\text{ V}$ $I_D = 100\text{ A}$ $R_g = 1\text{ }\Omega$ $V_{GS} = 10\text{ V}$	-	139	-	ns
Rise time	$t_r$		-	285	-	
Turn-off delay time	$t_{d(off)}$		-	120	-	
Fall time	$t_f$		-	142	-	
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ $V_{DS} = 25\text{ V}$ $f = 1\text{ MHz}$	-	13.7	-	nF
Output capacitance	$C_{oss}$		-	2.2	-	
Reverse transfer capacitance	$C_{rss}$		-	0.104	-	

SOURCE-DRAIN RATINGS AND CHARACTERISTICS ( $T_J = 25\text{ °C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Continuous source current (body diode)	$I_S$	MOSFET symbol showing the integral reverse p-n junction diode 	-	-	476	A
Pulsed source current (body diode)	$I_{SM}$		-	-	850	
Diode forward voltage	$V_{SD}$	$I_S = 250\text{ A}$ , $V_{GS} = 0\text{ V}$	-	0.95	-	V
Reverse recovery time	$t_{rr}$	$T_J = 25\text{ °C}$ , $I_F = I_S = 50\text{ A}$ , $dI/dt = 100\text{ A}/\mu\text{s}$ , $V_R = 50\text{ V}$	-	171	-	ns
Reverse recovery charge	$Q_{rr}$		-	1032	-	nC
Reverse recovery current	$I_{RM}$		-	12	-	A

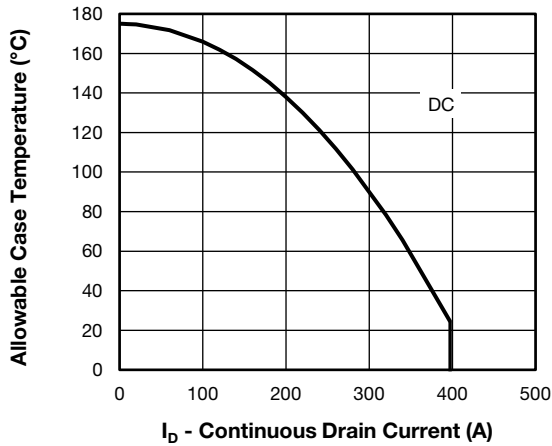


Fig. 1 - Maximum Continuous Drain Current vs. Case Temperature

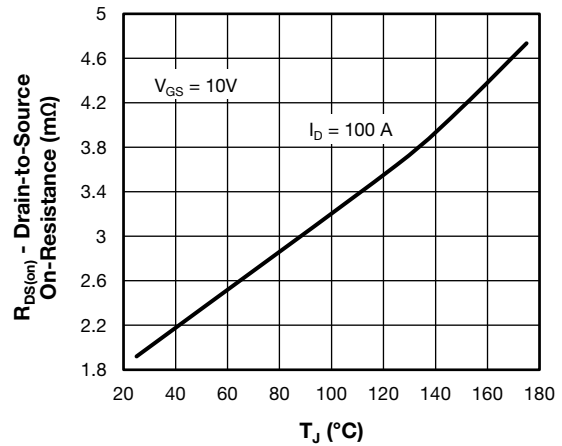


Fig. 4 - Typical Drain-to-Source On-Resistance vs. Temperature

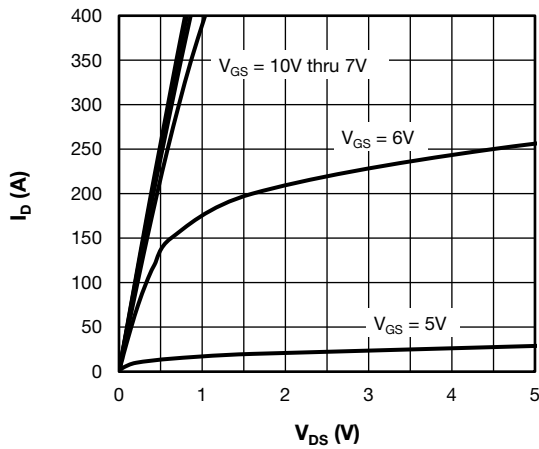


Fig. 2 - Typical Drain to Source Current Output Characteristics at  $T_J = 25\text{ }^\circ\text{C}$

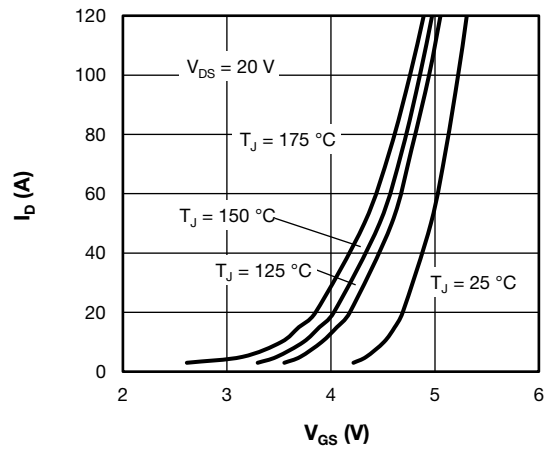


Fig. 5 - Typical Transfer Characteristics

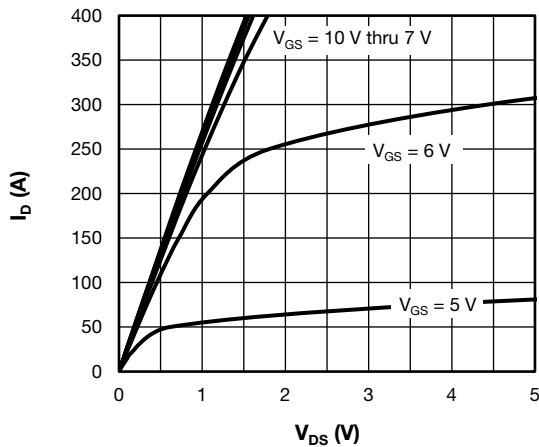


Fig. 3 - Typical Drain to Source Current Output Characteristics at  $T_J = 125\text{ }^\circ\text{C}$

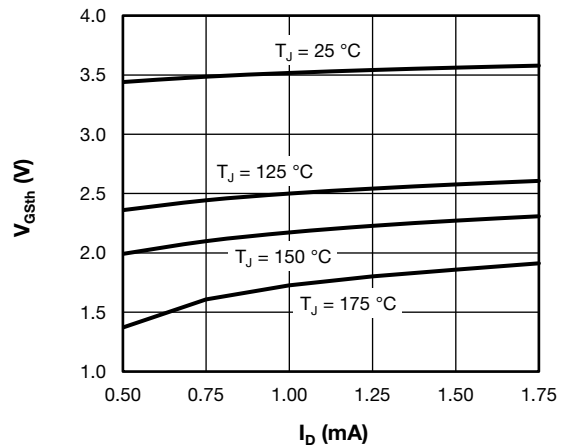


Fig. 6 - Typical Gate Threshold Voltage Characteristics

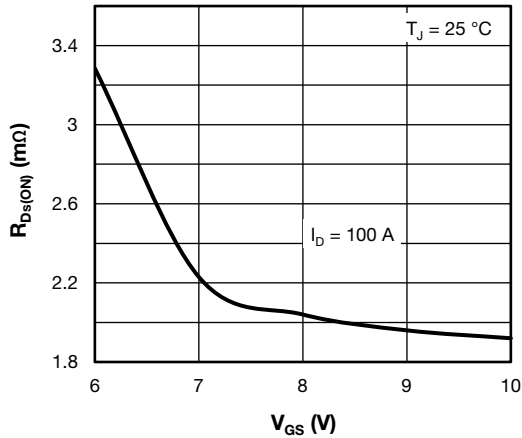


Fig. 7 - Typical Drain - State Resistance vs. Gate to Source Voltage

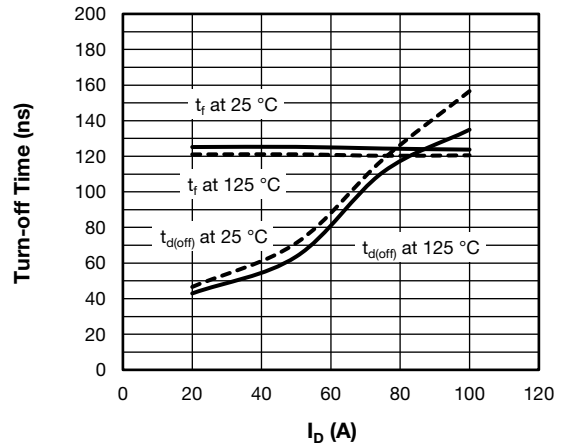


Fig. 10 - Typical Turn-off Switching Time vs.  $I_D$

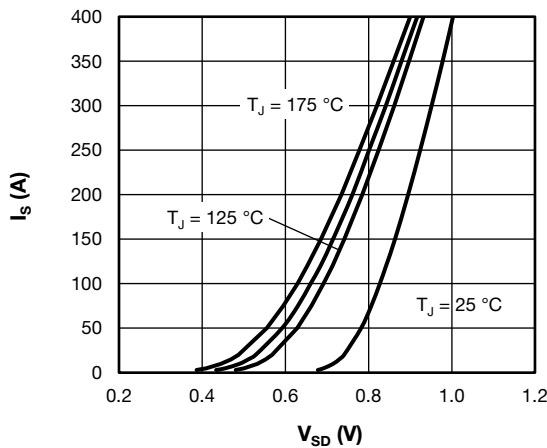


Fig. 8 - Typical Body Diode Source-to-Drain Current Characteristics

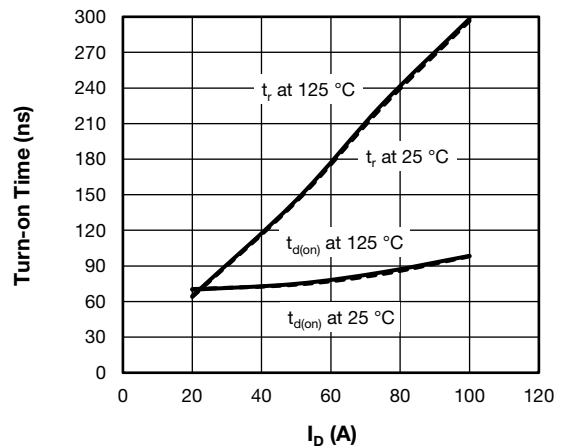


Fig. 11 - Typical Turn-on Switching Time vs.  $I_D$

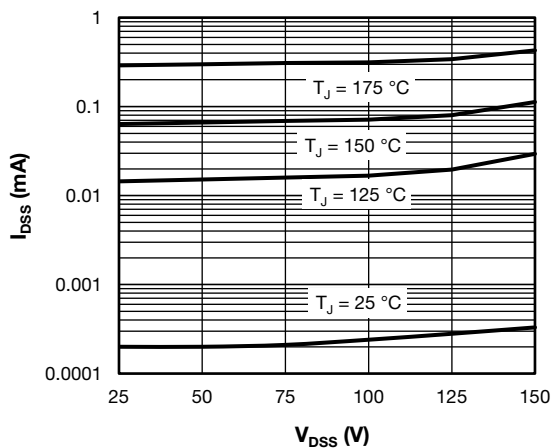


Fig. 9 - Typical Zero Gate Voltage Drain Current

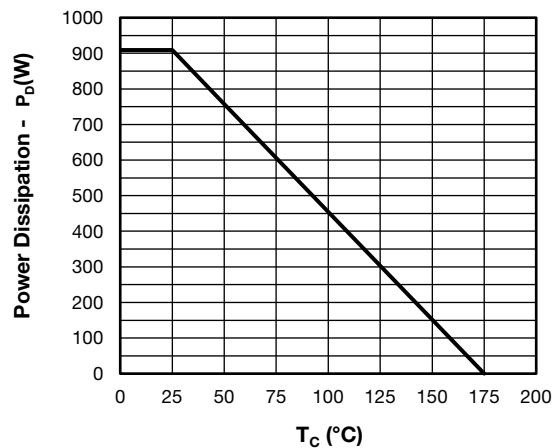


Fig. 12 - Power Dissipation Curve

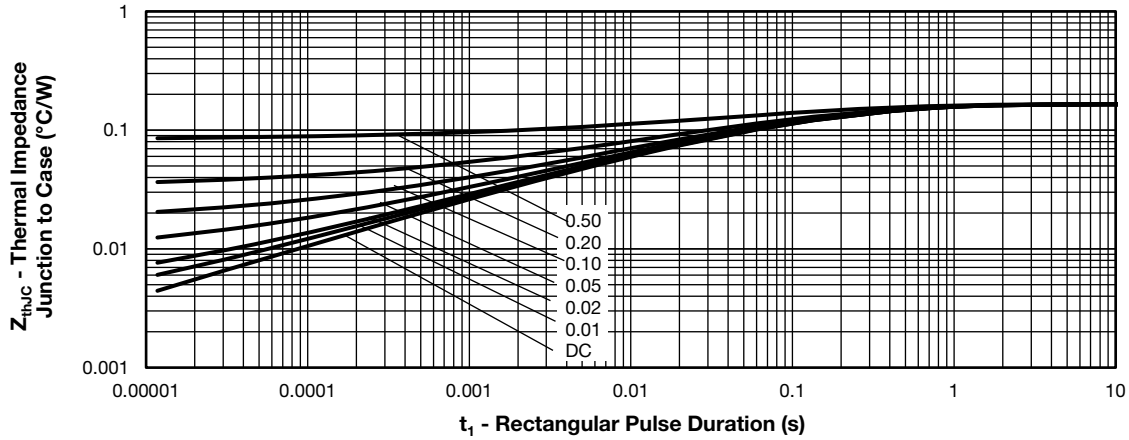


Fig. 13 - Maximum Thermal Impedance Junction-to-Case Characteristics

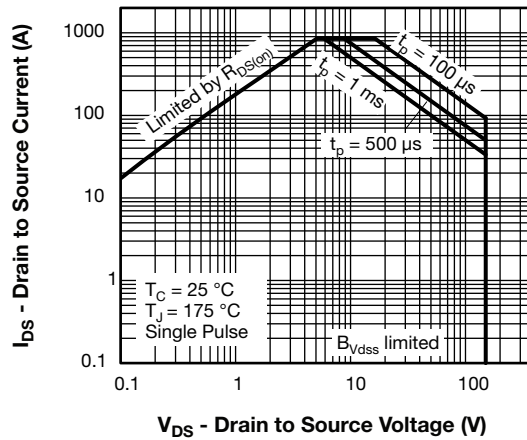


Fig. 14 - Safe Operating Area

**ORDERING INFORMATION TABLE**

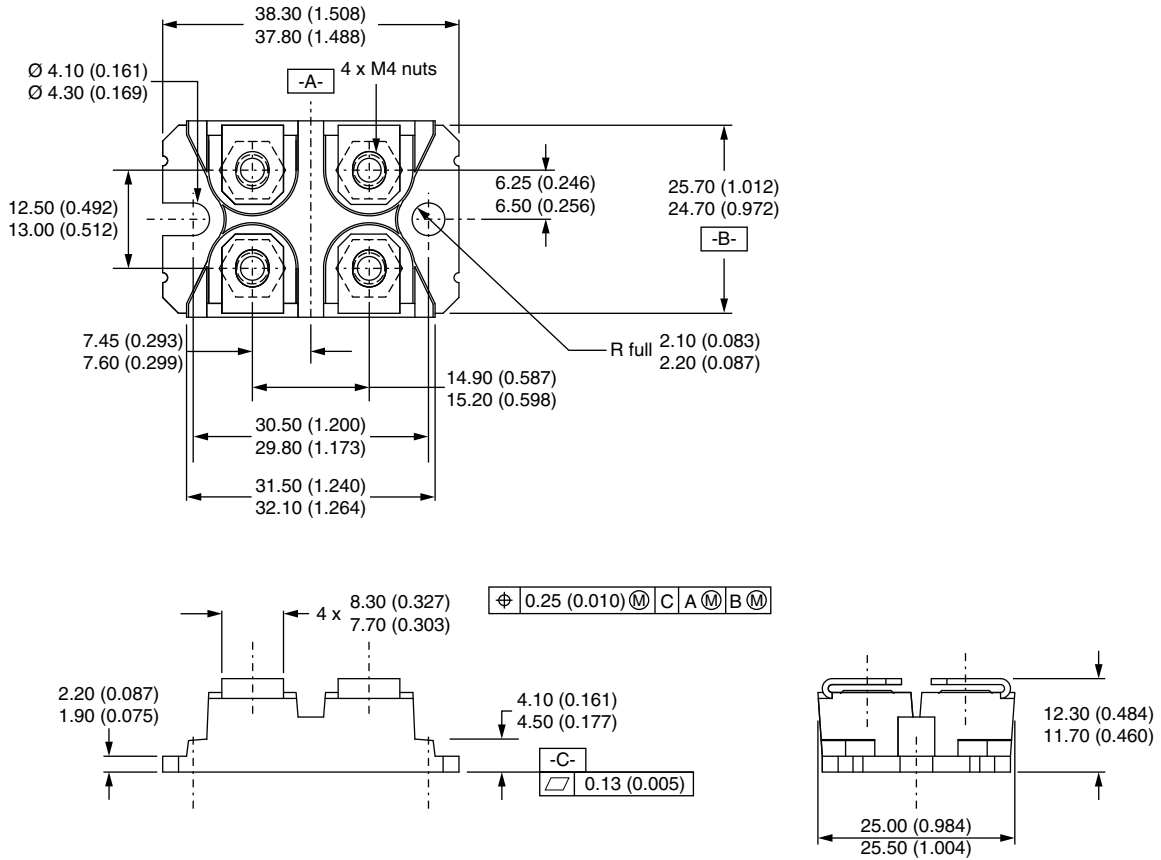
Device code	<b>VS-</b>	<b>F</b>	<b>C</b>	<b>420</b>	<b>S</b>	<b>A</b>	<b>15</b>
	①	②	③	④	⑤	⑥	⑦

- 1** - Vishay Semiconductors product
- 2** - MOSFET module
- 3** - MOSFET die generation
- 4** - Current rating (420 = 420 A)
- 5** - Circuit configuration (S = single switch)
- 6** - Package indicator (SOT-227)
- 7** - Voltage rating (15 = 150 V)

CIRCUIT CONFIGURATION		
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Single switch	S	<p>The circuit drawing for the 'Single switch' configuration (code S) consists of three parts:</p> <ul style="list-style-type: none"> <li><b>Schematic:</b> A circular schematic showing a diode and a switch. The diode is connected to terminal D (3). The switch is connected to terminal G (2). The other end of the switch is connected to terminal S (1-4).</li> <li><b>Lead Assignment:</b> A diagram of the component's physical layout with four pins labeled 1, 2, 3, and 4. Pin 1 is labeled (S), pin 2 is (G), pin 3 is (D), and pin 4 is (S).</li> <li><b>Circuit Diagram:</b> A detailed circuit diagram enclosed in a dashed box. It shows the internal connections between the pins: pin 3 (D) is connected to the diode, pin 2 (G) is connected to the switch, pin 4 (S) is connected to the other side of the diode, and pin 1 (S) is connected to the other side of the switch.</li> </ul>



**DIMENSIONS** in millimeters





## SOT-227 Generation 2

**DIMENSIONS** in millimeters (inches)



**Note**

- Controlling dimension: millimeter





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